

Application No.: 09/974,582

Docket No.: JCLA7521

In The Specification:

Please amend the paragraph starting at page 3, line 11 as follows:

Table 1 shows etching rate (ER, angstrom/minute) and the etching uniformity (U%) of nitrogen gas with respect to the silicon oxide and the silicon layer when the nitrogen gas is added in the plasma etching gas. When the flow rate of the nitrogen gas is 0 sccm, that is, the plasma etching gas contains no nitrogen, the etching rate of the silicon layer is 71 and the etching uniformity is 24.31%. When the flow rate of the nitrogen gas added is 10 sccm, the etching rate of the silicon layer is 224 and etching uniformity is 14.5%. When the flow rate of the nitrogen gas added is 30 sccm, the etching rate of the silicon layer is 403 and the etching uniformity is 10.5%. When the flow rate of the nitrogen gas added is 50 sccm, the etching rate of the silicon layer is 520 and the etching uniformity is 7.7%. Therefore, as the flow rate of the nitrogen gas increases, the etching rate of the silicon layer increases and the etching uniformity of the silicon layer decreases. The lower the value of the etching uniformity is, the higher etching uniformity is obtained.

In The Title:

Please amend the title as follows:

PLASMA ETCHING GAS ETCHING PROCESS